STY50N105DK5

N-channel 1050 V, 0.110 Ω typ., 46 A MDmesh™ DK5 Power MOSFET in a Max247 package

Datasheet - production data

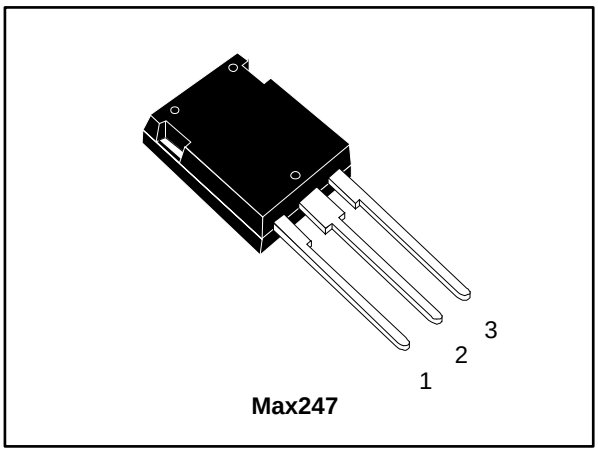
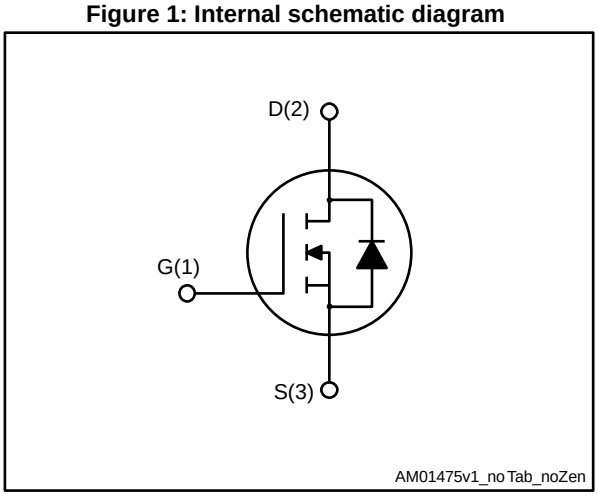


Figure 1: Internal schematic diagram



Features

Order code	V_{DS}	$R_{DS(on)}$ max.	I_D	P_{TOT}
STY50N105DK5	1050 V	0.120 Ω	46 A	625 W

- Fast-recovery body diode
- Best $R_{DS(on)}$ x area
- Low gate charge, input capacitance and resistance
- 100% avalanche tested
- Extremely high dv/dt ruggedness

Applications

- Switching applications

Description

This very high voltage N-channel Power MOSFET is part of the MDmesh™ DK5 fast recovery diode series. The MDmesh™ DK5 combines very low recovery charge (Q_{rr}) and recovery time (t_{rr}) with an excellent improvement in $R_{DS(on)}$ * area and one of the most effective switching behaviors, ideal for half bridge and full bridge converters.

Table 1: Device summary

Order code	Marking	Packages	Packaging
STY50N105DK5	50N105DK5	Max247	Tube

This is information on a product in full production.

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Contents

1 Electrical ratings

Table 2: Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{GS}	Gate-source voltage	±30	V
I_D	Drain current (continuous) at T_C = 25 °C	46	A
	Drain current (continuous) at T_C = 100 °C	30	A
I_{DM} (1)	Drain current (pulsed)	184	A
P_{TOT}	Total dissipation at T_C = 25 °C	625	W
dv/dt (2)	Peak diode recovery voltage slope	50	V/ns
dv/dt (3)	MOSFET dv/dt ruggedness	50	V/ns
T_j	Operating junction temperature range	-55 to 150	°C
T_{stg}	Storage temperature range		

Notes:

(1)Pulse width limited by safe operating area

(2)I_{SD} ≤ 23 A, di/dt ≤ 400 A/µs; $V_{DS\ peak}$ ≤ $V_{(BR)DSS}$, V_{DD} = 525 V

(3)V_{DS} ≤ 840 V

Table 3: Thermal data

Symbol	Parameter	Value	Unit
$R_{thj\text{-}case}$	Thermal resistance junction-case	0.2	°C/W
$R_{thj\text{-}amb}$	Thermal resistance junction-ambient	30	

Table 4: Avalanche characteristics

Symbol	Parameter	Value	Unit
I_{AS}	Single pulse avalanche energy (pulse width limited by T_{JMAX})	16	A
E_{AS}	Single pulse avalanche energy (starting T_J = 25°C, I_D = I_{AS}, V_{DD} = 50 V)	1550	mJ

2 Electrical characteristics

(T_{CASE} = 25 °C unless otherwise specified)

Table 5: On /off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	I_D = 1 mA, V_{GS} = 0 V	1050			V
I_{DSS}	Zero gate voltage drain current	V_{DS} = 1050 V, V_{GS} = 0 V			1	µA
		V_{DS} = 1050 V, V_{GS} = 0 V, T_C = 125 °C(1)			50	µA
I_{GSS}	Gate-body leakage current	V_{GS} = ±20 V, V_{DS} = 0 V			±10	µA
$V_{GS(th)}$	Gate threshold voltage	V_{DS} = V_{GS}, I_D = 100 µA	3	4	5	V
$R_{DS(on)}$	Static drain-source on-resistance	V_{GS} = 10 V, I_D = 23 A		0.110	0.120	Ω

Notes:

(1)Defined by design, not subject to production test

Table 6: Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	V_{DS} = 100 V, f = 1 MHz, V_{GS} = 0 V	-	6675	-	pF
C_{oss}	Output capacitance		-	370	-	pF
C_{rss}	Reverse transfer capacitance		-	10	-	pF
$C_{o(tr)}$(1)	Equivalent capacitance time related	V_{GS} = 0 V, V_{DS} = 0 to 840 V	-	630	-	pF
$C_{o(er)}$(2)	Equivalent capacitance energy related		-	219	-	
R_G	Intrinsic gate resistance	f = 1 MHz open drain	-	3	-	Ω
Q_g	Total gate charge	V_{DD} = 840 V, I_D = 46 A, V_{GS} = 10 V (see *Figure 15: "Test circuit for gate charge behavior"*)	-	204	-	nC
Q_{gs}	Gate-source charge		-	36	-	nC
Q_{gd}	Gate-drain charge		-	133	-	nC

Notes:

(1)Time related is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}.

(2)Energy related is defined as a constant equivalent capacitance giving the same stored energy as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}.

Table 7: Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	V_{DD} = 525 V, I_D = 23 A, R_G = 4.7 Ω, V_{GS} = 10 V (see *Figure 14: "Test circuit for resistive load switching times"* and *Figure 19: "Switching time waveform"*)	-	40.6	-	ns
t_r	Rise time		-	64.5	-	ns
$t_{d(off)}$	Turn-off delay time		-	262	-	ns
t_f	Fall time		-	49.5	-	ns

Table 8: Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		46	A
I_{SDM}	Source-drain current (pulsed)		-		184	A
V_{SD}(1)	Forward on voltage	I_{SD} = 46 A, V_{GS} = 0 V	-		1.5	V
t_{rr}	Reverse recovery time	I_{SD} = 46 A, V_{DD} = 60 V, di/dt = 100 A/µs (see *Figure 16: "Test circuit for inductive load switching and diode recovery times"*)	-	273		ns
Q_{rr}	Reverse recovery charge		-	3		µC
I_{RRM}	Reverse recovery current		-	23		A
t_{rr}	Reverse recovery time	I_{SD} = 46 A, V_{DD} = 60 V, di/dt = 100 A/µs, T_j = 150 °C (see *Figure 16: "Test circuit for inductive load switching and diode recovery times"*)	-	477		ns
Q_{rr}	Reverse recovery charge		-	10		µC
I_{RRM}	Reverse recovery current		-	42		A

Notes:

(1)Pulsed: pulse duration = 300 µs, duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 2: Forward bias safe operating area

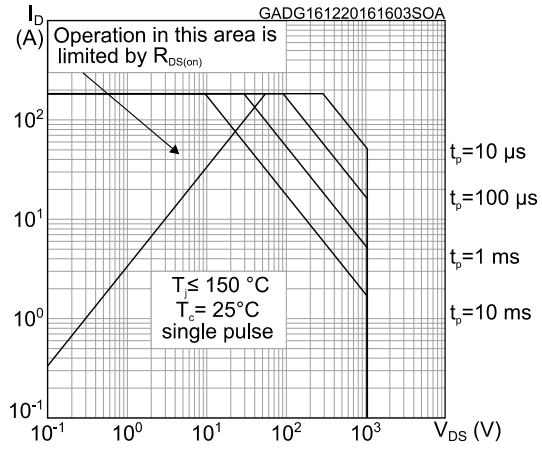


Figure 3: Thermal impedance

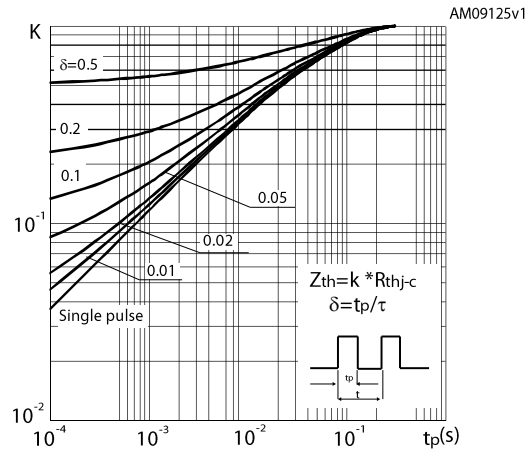


Figure 4: Output characteristics

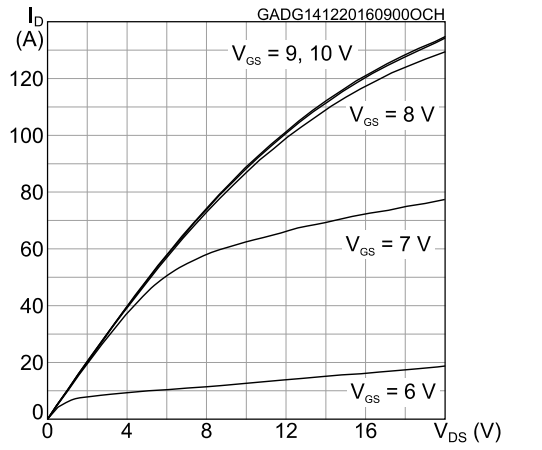


Figure 5: Transfer characteristics

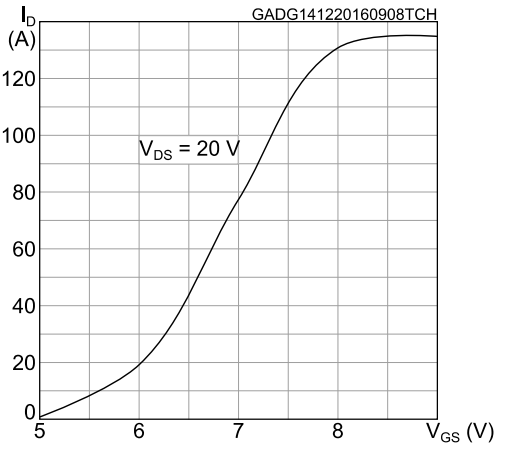


Figure 6: Gate charge vs gate-source voltage

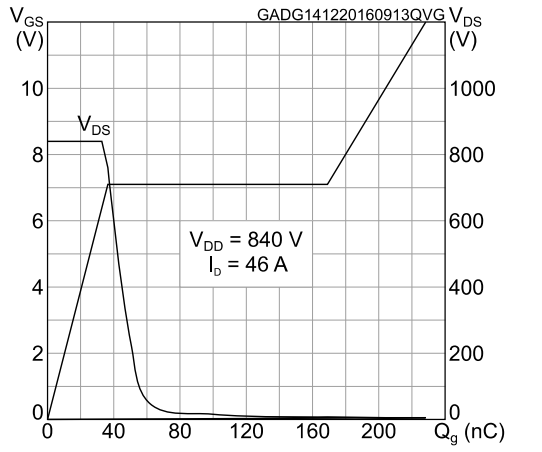


Figure 7: Static drain-source on-resistance

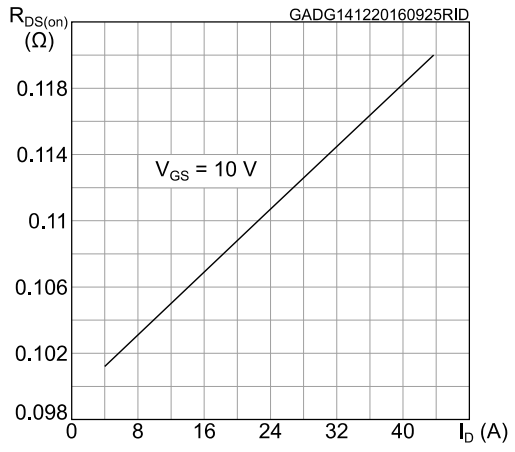


Figure 8: Capacitance variations

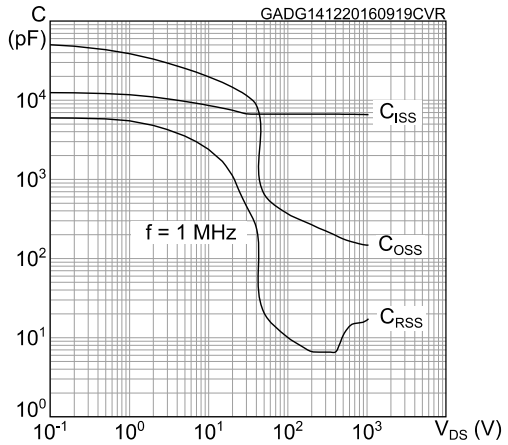


Figure 9: Normalized gate threshold voltage vs temperature

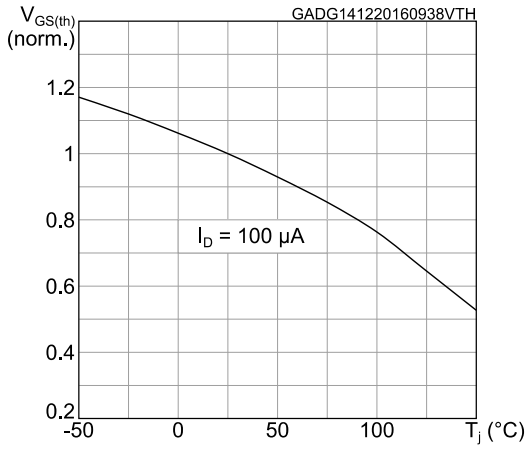


Figure 10: Normalized on-resistance vs temperature

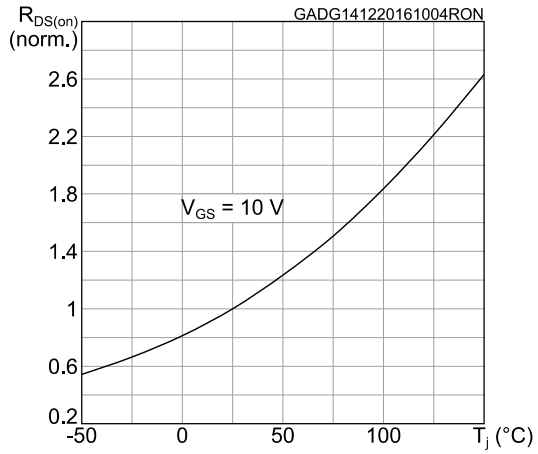


Figure 11: Normalized $V_{(BR)DSS}$ vs temperature

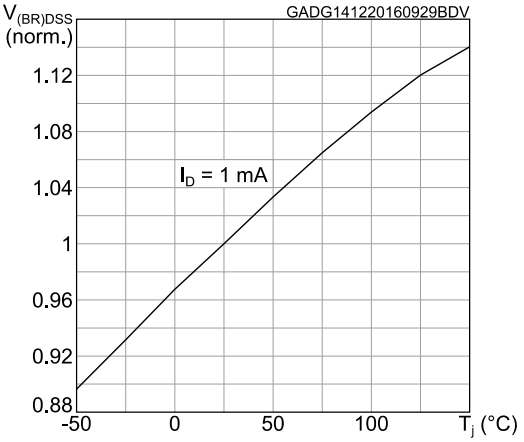


Figure 12: Source-drain diode forward characteristics

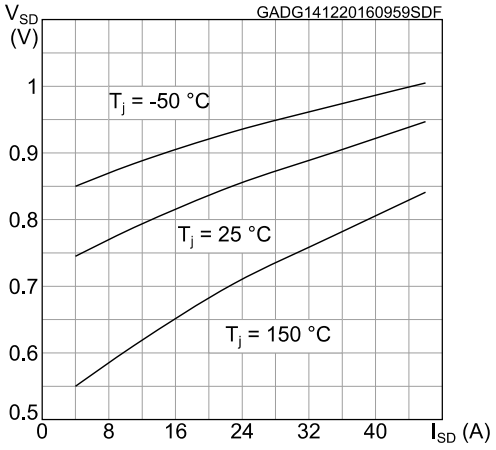
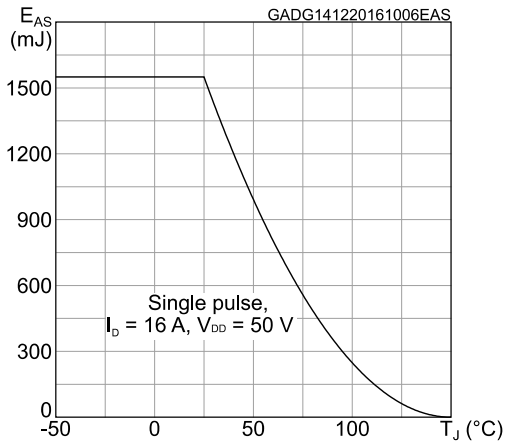


Figure 13: Maximum avalanche energy vs starting T_J



3 Test circuits

Figure 14: Test circuit for resistive load switching times

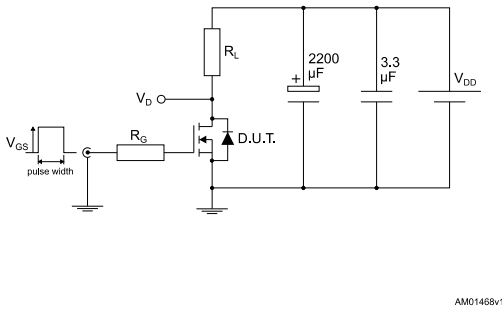


Figure 15: Test circuit for gate charge behavior

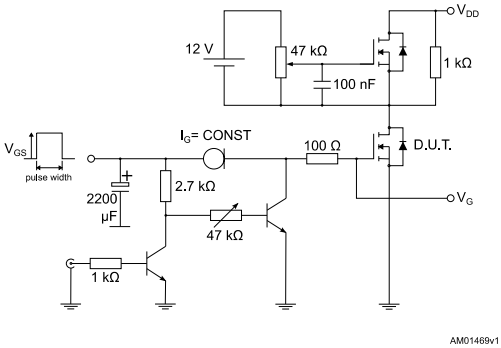


Figure 16: Test circuit for inductive load switching and diode recovery times

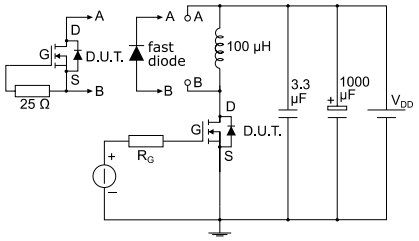


Figure 17: Unclamped inductive load test circuit

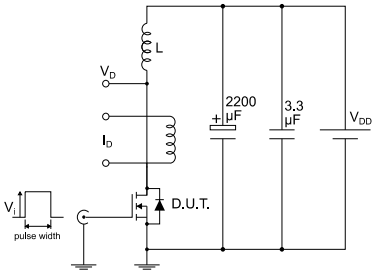


Figure 18: Unclamped inductive waveform

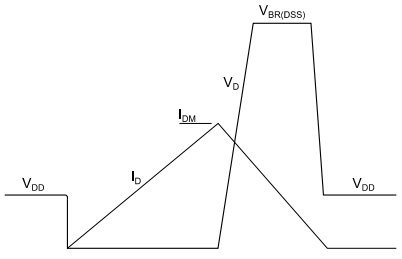
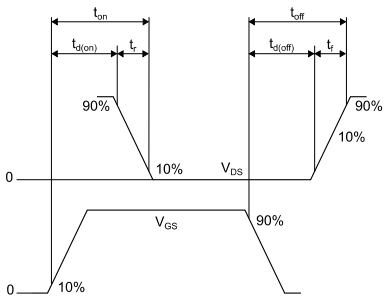


Figure 19: Switching time waveform



4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: ***www.st.com***. ECOPACK® is an ST trademark.

4.1 Max247 package information

Figure 20: Max247 package outline

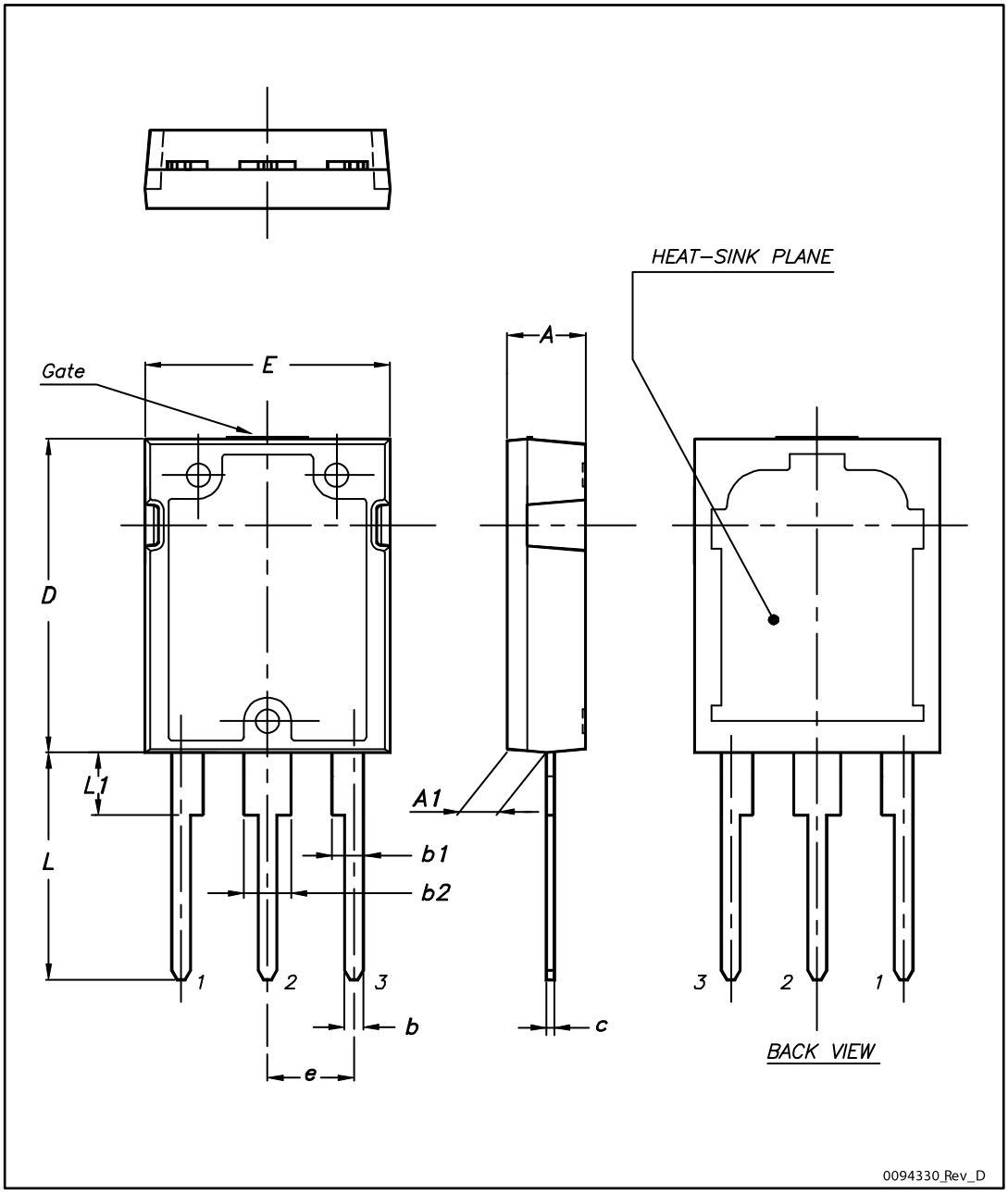


Table 9: Max247 package mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.70	-	5.30
A1	2.20	-	2.60
b	1.00	-	1.40
b1	2.00	-	2.40
b2	3.00	-	3.40
c	0.40	-	0.80
D	19.70	-	20.30
e	5.35	-	5.55
E	15.30	-	15.90
L	14.20	-	15.20
L1	3.70	-	4.30

5 Revision history

Table 10: Document revision history

Date	Revision	Changes
24-Jan-2013	1	First release
19-Dec-2016	2	Datasheet status promoted from preliminary to production data. Updated features, description and internal schematic diagram on cover page. Updated *Section 1: "Electrical ratings"* and *Section 2: "Electrical characteristics"*. Minor text changes

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